

1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-0100

2. Structure :

- 2-1. Planar type : PIN diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy.

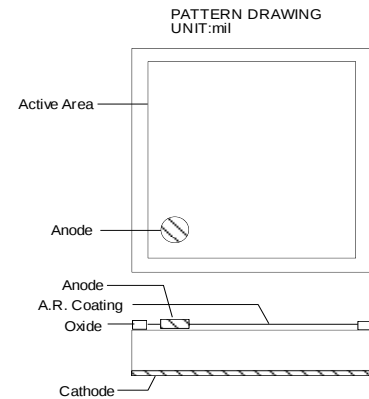
3. Size :

- 3-1. Chip size : 100 mils × 100 mils (2.540 mm × 2.540 mm).
3-2. Chip thickness : 12 ± 1.5 mils (0.305 ± 0.038 mm).
3-3. Active area : 90 mils × 90 mils (2.250 mm × 2.250 mm).
3-4. Bonding pad (Anode) : 5.5 mils (0.140 mm) diameter.
3-5. Pattern drawing : refer to the attached drawing.

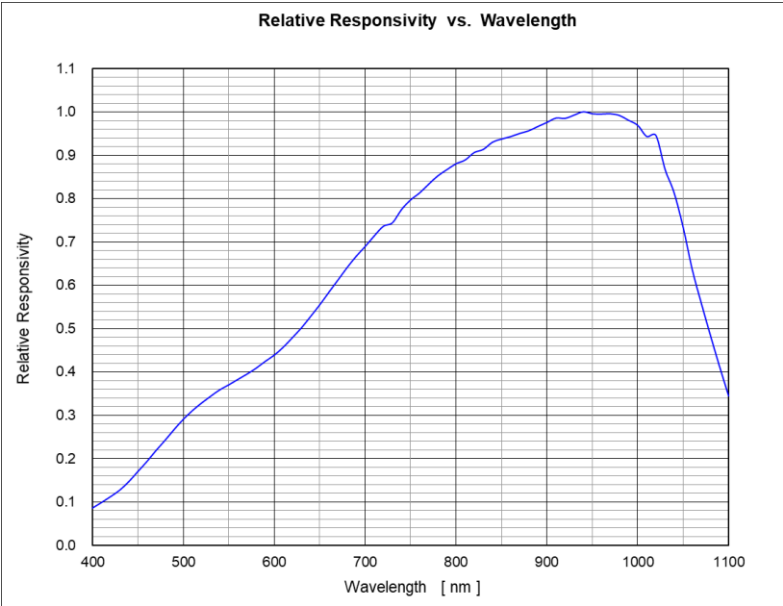
4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse dark Current	I_D	$V_R=10V$ $E_e=0mW/cm^2$			30	nA
*Reverse breakdown Voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	33			V
Open circuit Voltage	V_{oc}	$T=2856K$ $E_e=5mW/cm^2$		390		mV
Short circuit Current	I_{sc}	$T=2856K$ $E_e=5mW/cm^2$		51		μA
Reverse light current	I_L	$V_R=5V$ $T=2856K$ $E_e=5mW/cm^2$		51		μA
Total Capacitance	C_t	$V_R=5V$ $E_e=0mW/cm^2$ $f=1MHz$		14		pF
Turn-on/ Turn-off Time	ton/toff	$V_R=5V$ $R_L=50\Omega$ $\lambda=850nm$		50/50		nS

*Based on 100% probing



5. Relative spectral responsivity



※ Bare chip measured with integrating sphere, for reference only.